



## NTP13N10G Information



For Reference Only

Part Number NTP13N10G

Manufacturer ON Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 100V 13A TO220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# NTP13N10G Specifications

Manufacturer Part Number         NTP13N10G           Manufacturer         ON Semiconductor           Category         Discrete Semiconductor Products           Package         TO-220-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         100V           Current - Continuous Drain (Id) @ 25°C         13A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         20nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         550pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         64.7W (Tc)           Rds On (Max) @ Id, Vgs         165 mOhm @ 6.5A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB		
CategoryDiscrete Semiconductor ProductsPackageTO-220-3Series-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C13A (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs20nC @ 10VInput Capacitance (Ciss) (Max) @ Vds550pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)64.7W (Tc)Rds On (Max) @ Id, Vgs165 mOhm @ 6.5A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough Hole	Manufacturer Part Number	NTP13N10G
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Operating Temperature $-55^{\circ}\text{C} \sim 175^{\circ}\text{C} \text{ (TJ)}$ Mounting Type Through Hole	Power Dissipation (Max)	64.7W (Tc)
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	Operating Temperature	-55°C ~ 175°C (TJ)
Supplier Device Package TO-220AB	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Package / Case TO-220-3	Package / Case	TO-220-3
Report errors?		Report errors?

#### NTP13N10G Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## NTP13N10G Payment Methods



















## NTP13N10G Shipping Methods













If you have any question about NTP13N10G, please do not hesitate to contact us!

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